

# **Structural, chemical, and thermoelectric properties of $\text{Bi}_2\text{Te}_3$ Peltier materials: bulk, thin film, and superlattices**

**Struktur, chemische Zusammensetzung und physikalische Eigenschaften von  $\text{Bi}_2\text{Te}_3$  Peltier-Materialien: Volumenmaterialien, Dünnschichten und Übergitterstrukturen**

Nicola Peranio

**Correlations structure-chemical composition-thermoelectric properties**

**Transmission electron microscopy (TEM)**

**$\text{Bi}_2\text{Te}_3$  thin film and  $\text{Bi}_2\text{Te}_3/\text{Bi}_2(\text{Te},\text{Se})_3$  superlattice structures**

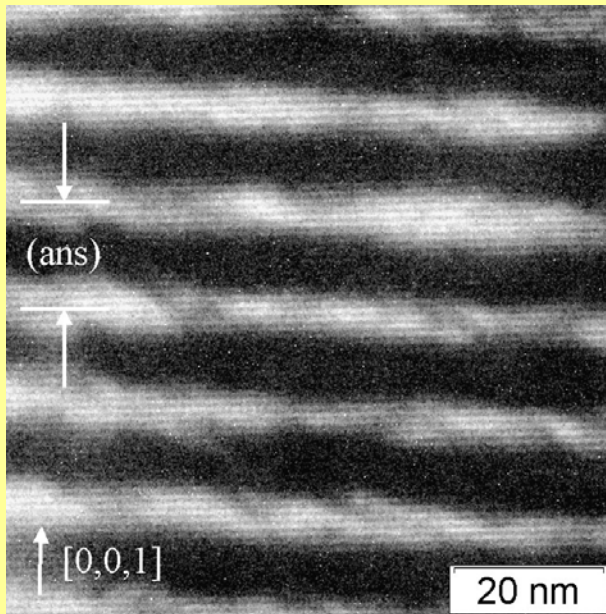
**$\text{Bi}_2(\text{Te},\text{Se})_3$  and  $(\text{Bi},\text{Sb})_2\text{Te}_3$  bulk**

## Thermoelectric properties, structural and chemical modulations (on the nanometer scale)

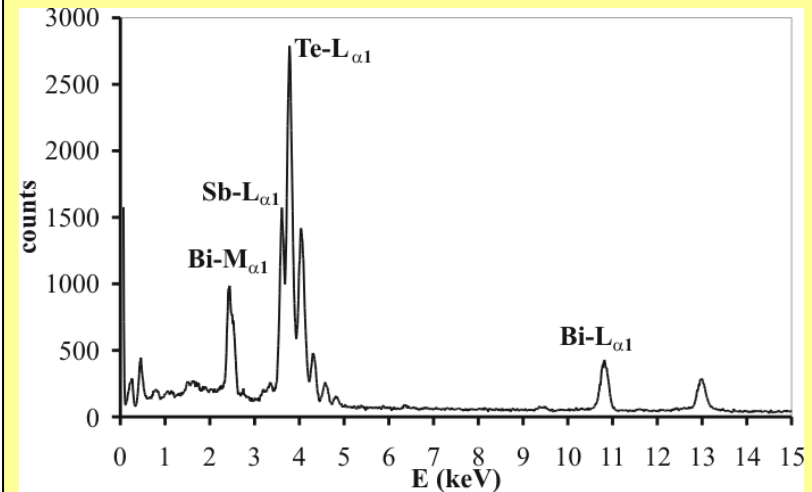
thermoelectric figure of merit:  $ZT = \frac{S^2 \sigma}{\lambda_{\text{el}} + \lambda_{\text{latt}}} T \approx 1$  at 300K

$\text{Bi}_2\text{Te}_3$ :  $S \approx 200 \mu\text{V/K}$ ,  $\sigma \approx 1000 \text{ 1}/\Omega\text{cm}$ ,  $\lambda \approx 1 \text{ W/mK}$

### nanostructure



### chemical composition



correlation ?

processing of bulk, thin films, superlattices

start

to verify

## bulk

- chemical composition and extended crystal defects determine transport properties
- local variations in stoichiometry
- Character and density of extended crystal defects

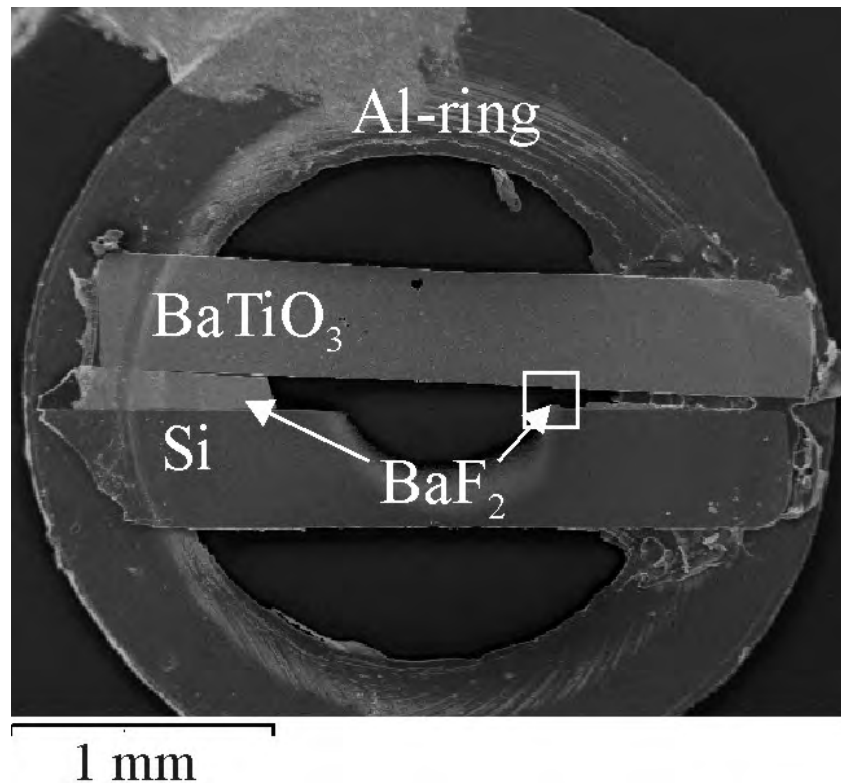
## superlattices

- chemical composition
- Epitaxial relations
- superlattice period
- thermoelectric properties
- Layer and interface roughness
- Extended crystal defects and interaction with superlattices

# Transmission electron microscopy

## Zeiss912Ω TEM

- 120 keV
- CCD camera, video CCD camera
- double-tilt holder, tilt range 60°/30°
- energy-dispersive X-ray detector (EDX)
- in-column OMEGA energy-filter



# Bi<sub>2</sub>Te<sub>3</sub>: thin films and superlattices

Hicks & Dresselhaus, Phys. Rev. B **47**, 12727 (1993):  
quantum well with width  $a$ :

$$ZT \propto \frac{\mu}{\lambda_{\text{latt}}} \frac{1}{a}$$

Venkatasubramanian, Nature **413**, 597 (2001):  
Bi<sub>2</sub>Te<sub>3</sub>/Sb<sub>2</sub>Te<sub>3</sub> SL, period 6 nm → **ZT=2.4**

Fraunhofer IPM:

- Bi<sub>2</sub>Te<sub>3</sub> thin films (1μm)
- symmetric Bi<sub>2</sub>Te<sub>3</sub>/Bi<sub>2</sub>(Te<sub>0.88</sub>Se<sub>0.12</sub>)<sub>3</sub> SL,  
film thickness 1μm, period 6 nm and 12 nm

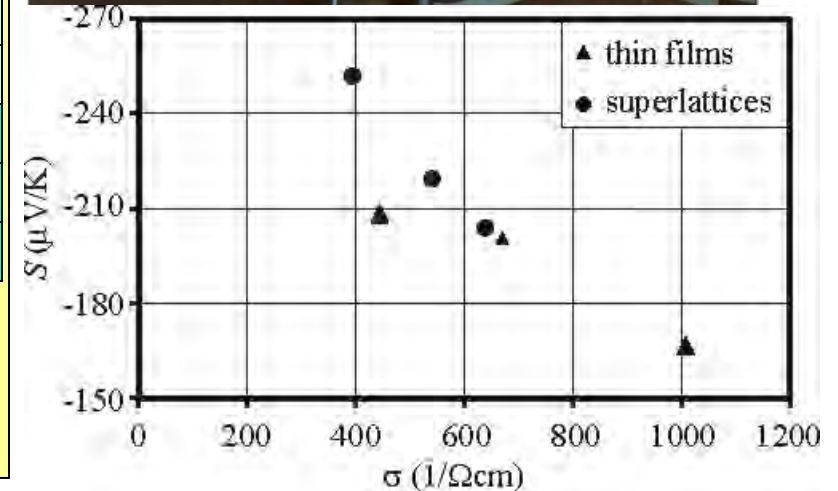
Material	Structure	$\mu$ cm <sup>2</sup> /Vs	$\lambda_{\text{latt}}$ (W/mK)	ZT
Bi <sub>2</sub> Te <sub>3</sub>	bulk	160	1.53	0.46
Bi <sub>2</sub> (Te,Se) <sub>3</sub>	bulk	150	1.15	0.85
Bi <sub>2</sub> Te <sub>3</sub>	thin film	120	1.60	0.45
Bi <sub>2</sub> Te <sub>3</sub> /Bi <sub>2</sub> (Te,Se) <sub>3</sub>	SL-12nm		1.07	
Bi <sub>2</sub> Te <sub>3</sub> /Bi <sub>2</sub> (Te,Se) <sub>3</sub>	SL-10nm	100	1.01	0.60

→ reduction of carrier mobility  $\mu$

→ reduction of lattice thermal conductivity  $\lambda_{\text{latt}}$

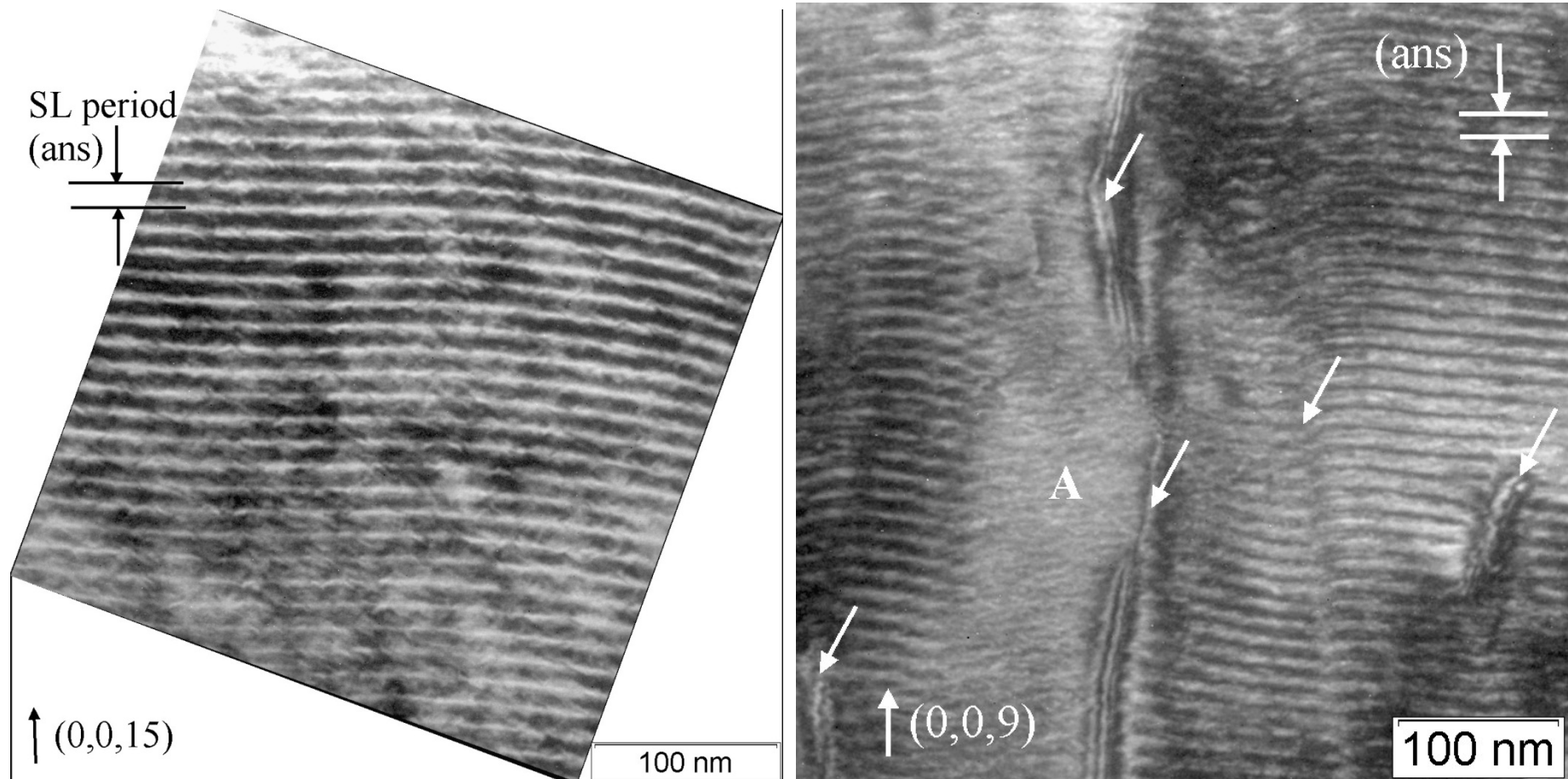
→ no  $ZT$  enhancement

MBE:(111)-BaF<sub>2</sub> substrate,  
 $T_s=290^\circ\text{C}$ ; lattice mismatch: 0.05%  
(in-plane measurements, 300K)





## $\text{Bi}_2\text{Te}_3$ superlattice (12nm) in cross section



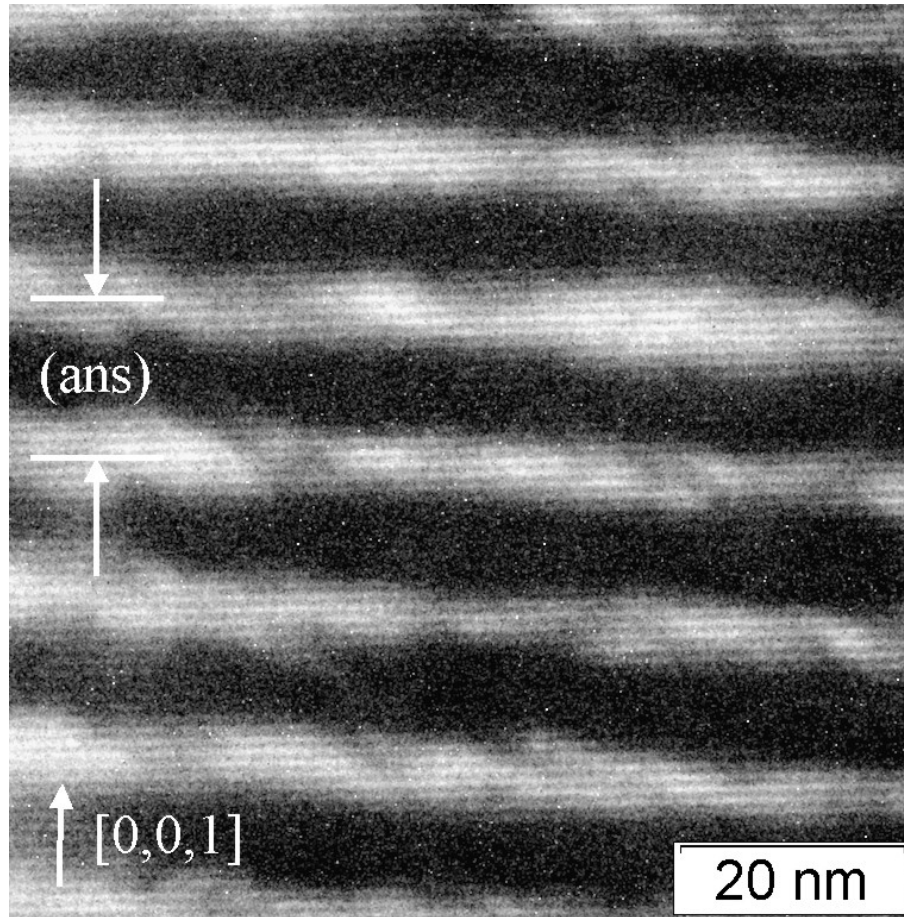
### **superlattice (ans)**

- period 12.0 nm,
- slight bending, amplitude 30 nm, wavelength 400 nm

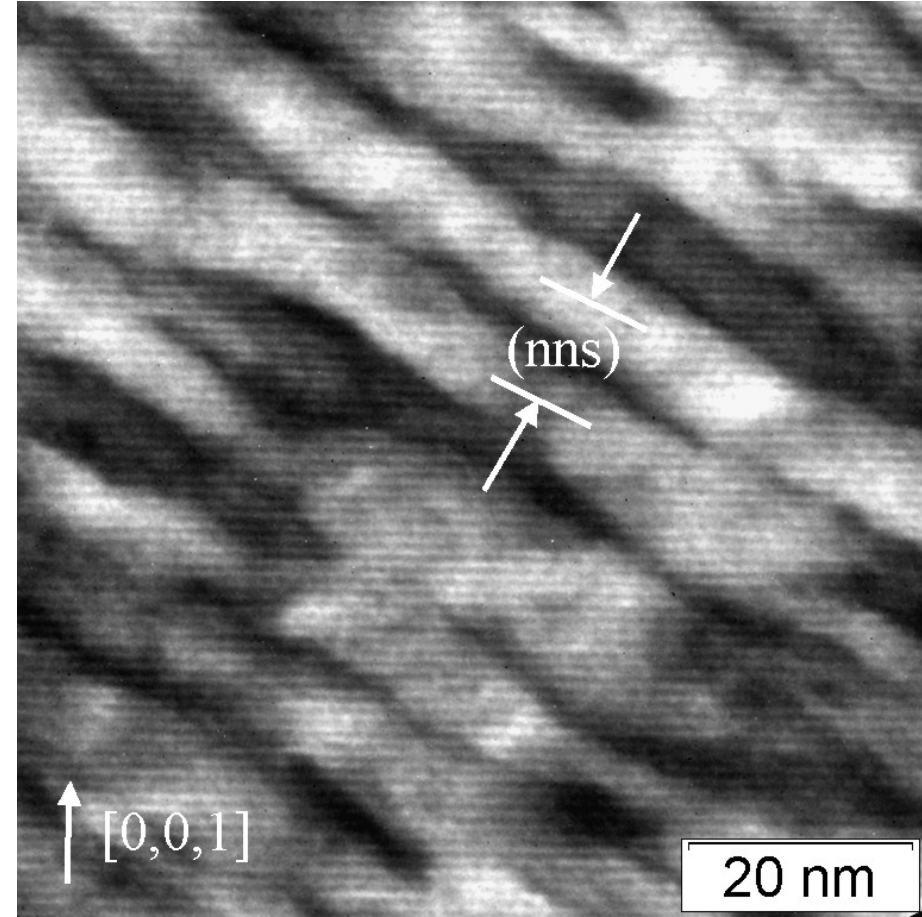
- threading dislocations with density of  $2 \times 10^9 \text{cm}^{-2}$
- strong bending of the superlattice
- SL disappeared in region A

## High resolution images of the $\text{Bi}_2\text{Te}_3$ superlattice (12nm) in cross section

nns out of contrast



nns in contrast



### superlattice (ans)

- period 12.0 nm
- no bending of the SL due to nns

### structural modulation (nns)

- wavelength 10 nm and wave vector (1,0,10)
- no bending of the nns due to SL

## Superlattices, artificial nanostructures (ans)

1. The superlattice structure (ans) can be imaged with strongly excited (0,0,1)-reflections.
2. The SL showed a period of 12.0 nm, bending with an amplitude of 30 nm and a wavelength of 400 nm, and threading dislocations with a density of  $2 \times 10^9 \text{ cm}^{-2}$ .
3. The lattice thermal conductivity  $\lambda_{\text{latt}}$  decreases with decreasing SL period; therefore, superlattices yield an enhanced scattering of phonons.
4. A nns is superimposed to the structure, yielding a significant amount of stress in the samples, which was still not noticed and identified. The stress fields directly affect the transport coefficients, particularly the lattice thermal conductivity.
5. The thermopower and the electrical conductivity were found to be negatively correlated, depend on the charge carrier density, and no clear dependence of the two quantities on the microstructure could be found.

**N. Peranio, O. Eibl, and J. Nurnus, „Structural and thermoelectric properties of epitaxially grown  $\text{Bi}_2\text{Te}_3$  thin films and superlattices“, J. Appl. Phys. 100, 114306 (2006).**



# Bi<sub>2</sub>Te<sub>3</sub> bulk materials

**Crystal structure:** pseudo-hexagonal (a=0.44 nm, c=3.05 nm)

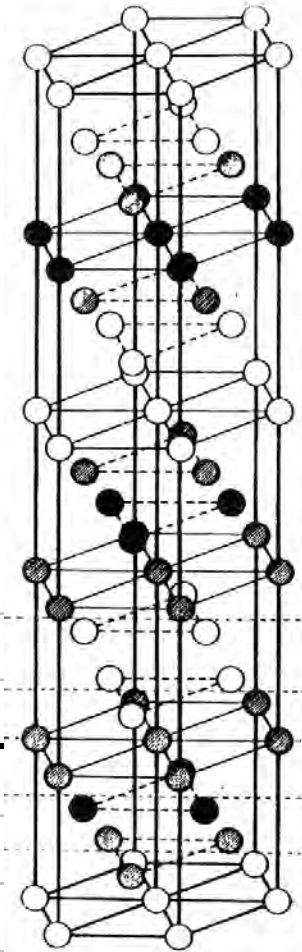
## Peltron samples:

- n-type Bi<sub>2</sub>(Te<sub>0.91</sub>Se<sub>0.09</sub>)<sub>3</sub>
- p-type (Bi<sub>0.26</sub>Sb<sub>0.74</sub>)<sub>1.98</sub>(Te<sub>0.99</sub>Se<sub>0.01</sub>)<sub>3.02</sub>
- synthesized by the Bridgman technique
- good texture, grain size 5 μm

## Thermoelectric properties (300 K, in-plane):

D.M. Rowe, *CRC Handbook of Thermoelectrics*

sample	n/p	μ	σ	S	S <sup>2</sup> σ	λ	λ <sub>latt</sub>	ZT
	10 <sup>19</sup> cm <sup>-3</sup>	cm <sup>2</sup> /Vs	1/Ωcm	μV/K	μW/cmK <sup>2</sup>	W/mK	W/mK	
Bi <sub>2</sub> Te <sub>3</sub>	2.00	160	513	227	26	1.73	1.53	0.46
Bi <sub>2</sub> (Te <sub>0.95</sub> ,Se <sub>0.05</sub> ) <sub>3</sub>	4.00	150	901	-223	45	1.59	1.15	0.85
(Bi <sub>0.25</sub> ,Sb <sub>0.75</sub> ) <sub>2</sub> Te <sub>3</sub>	3.34	177	781	225	40	1.37	1.07	0.87



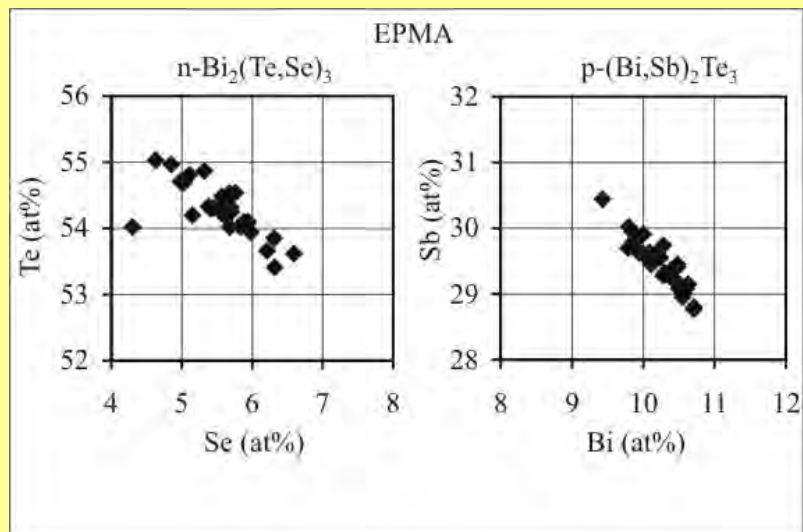
- reduction of lattice thermal conductivity due to **alloy scattering** of the phonons
- *ZT* enhancement

## Knowledge about structure and chemical composition:

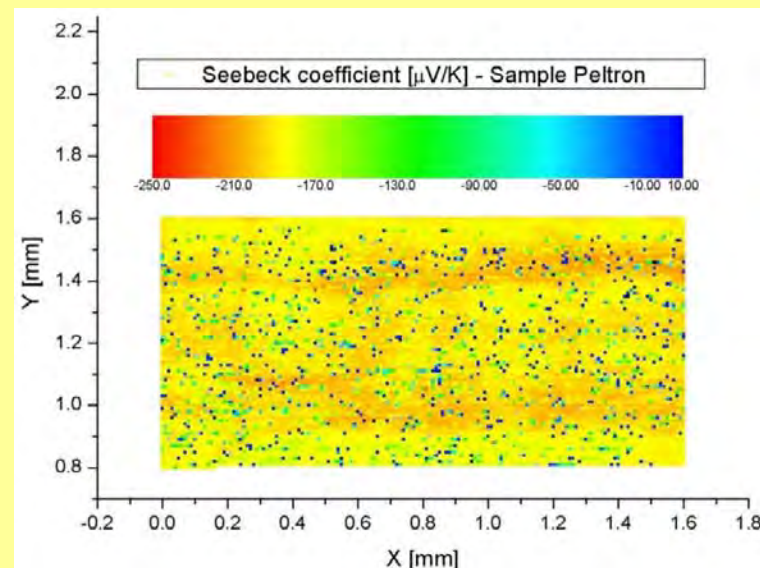
- Bi<sub>2</sub>Te<sub>3</sub> shows a low lattice thermal conductivity λ<sub>latt</sub> like a highly disordered material
- no experimental results specified what the structural disorder would be
- Bi<sub>2</sub>Te<sub>3</sub> alloys are assumed to be solid solutions

## Chemical analysis and Seebeck scanning microprobe (SPM)

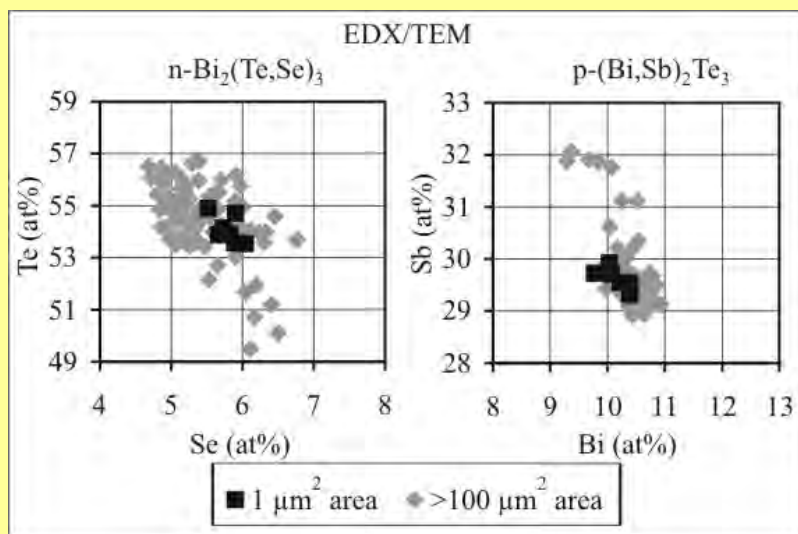
### EPMA: lateral resolution 1 $\mu\text{m}$



### SPM: lateral resolution 20 $\mu\text{m}$



### EDX in the TEM: lateral resolution 50 nm



→ variations in stoichiometry on the micrometer scale

$\pm 1.5$  at% Te/Se in n-type

Bi<sub>2</sub>(Te,Se)<sub>3</sub>

$\pm 1.5$  at% Bi/Sb in p-type

(Bi,Sb)<sub>2</sub>Te<sub>3</sub>

→ variations in thermopower on the micrometer scale

$-192 \pm 9$   $\mu\text{V/K}$

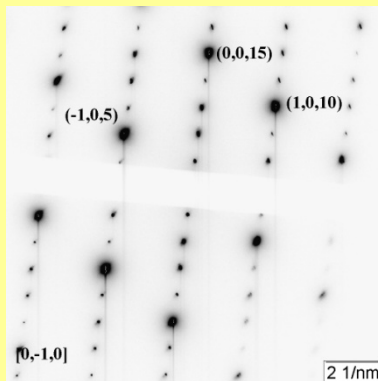
N. Peranio and O. Eibl, „Quantitative EDX microanalysis of Bi<sub>2</sub>Te<sub>3</sub> in the TEM”, Phys. Status Solidi A 204, 3243 (2007).

## Stereomicroscopy (tomography):

acquisition of two-beam images+ tilt series

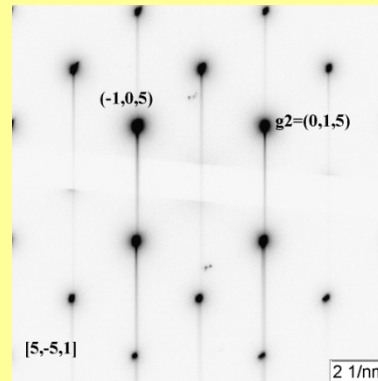
→ character of dislocations

pole 1



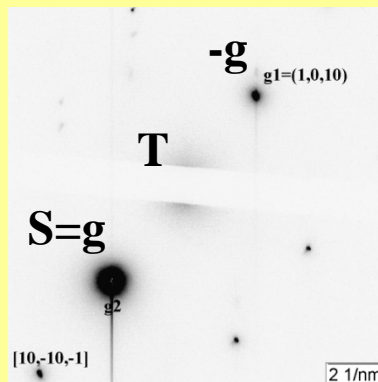
50° tilt

pole 2



10° tilt

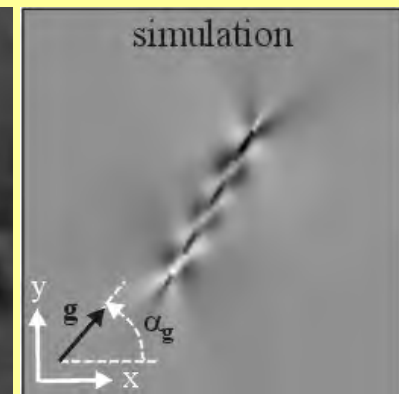
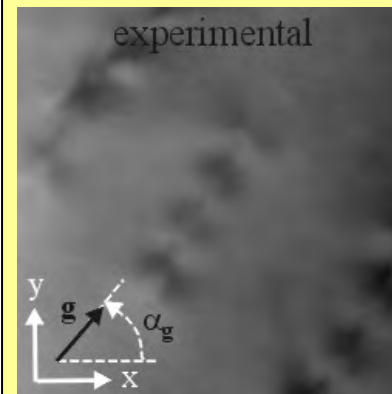
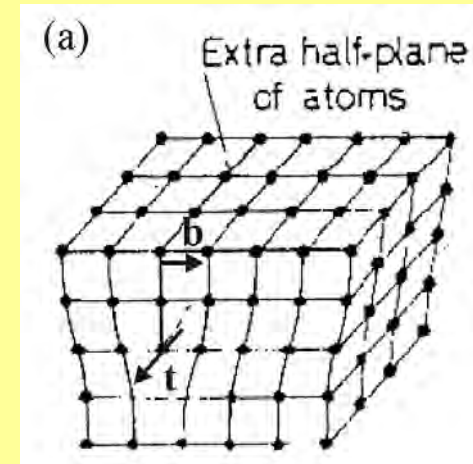
Two-beam condition  
for Bragg-reflection  $g$



## Dislocation:

bending of lattice planes  $g$

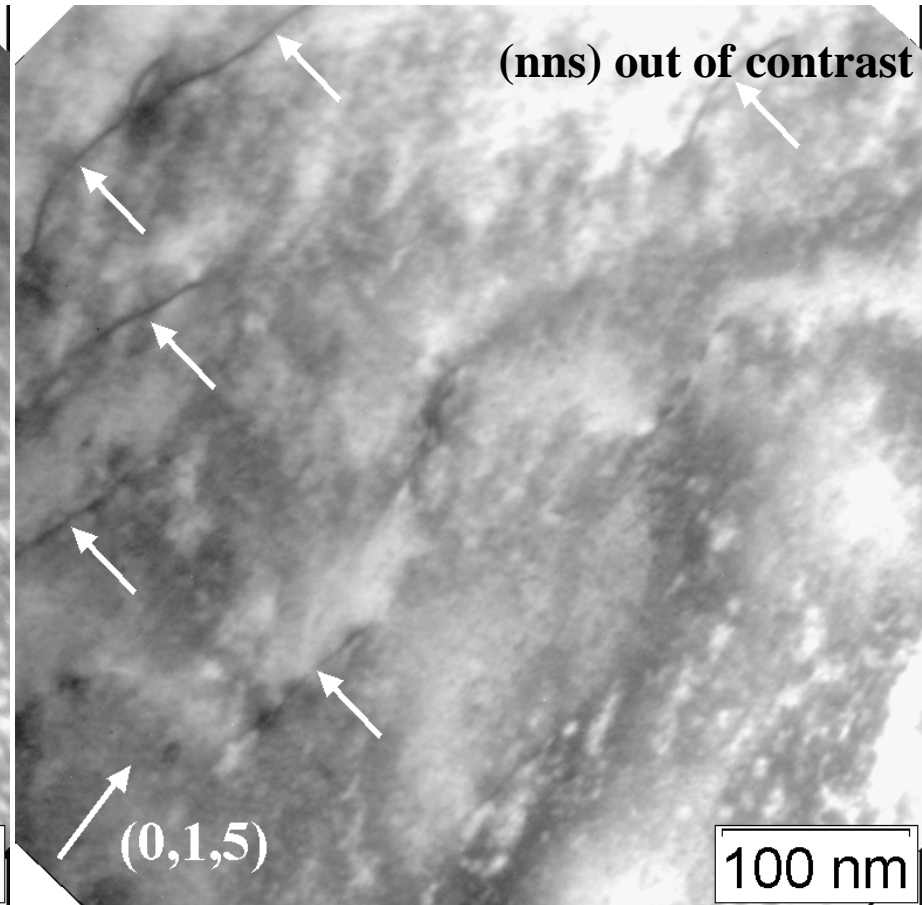
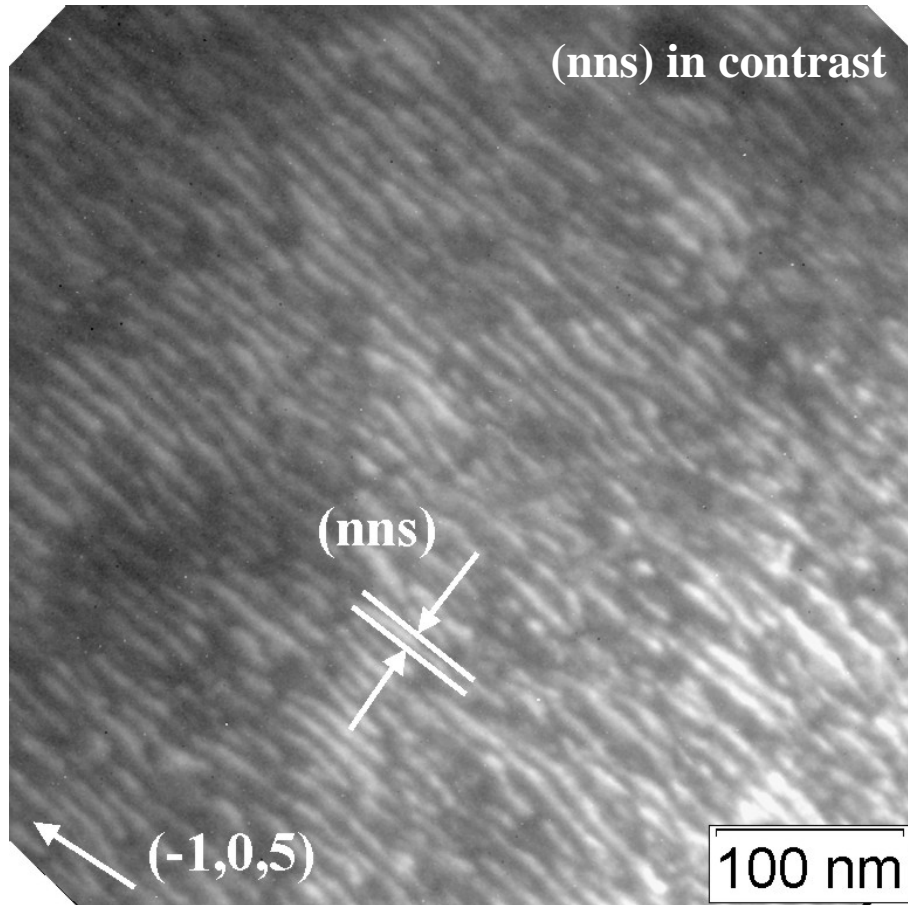
→ strain contrast under two-beam condition



Dislocation (strain field)  
out of contrast:

$$\vec{g} \cdot \vec{b} = 0 \quad \vec{g} \cdot \vec{u} = 0$$

## nns and gliding dislocations in n-type $\text{Bi}_2\text{Te}_3$



### structural modulation (nns):

sinusoidal displacement field

$$\mathbf{u} = \mathbf{u}_0 \cdot \sin(\mathbf{q} \cdot \mathbf{x})$$

wavelength 10 nm,

wave vector  $\mathbf{q}$ :  $(1,0,10)$ ,

displacement vector  $\mathbf{u}_0$ :  $[-10,-5,1]$

reflection $\mathbf{g}$	(nns) in contrast ?
$(-1,0,5)$	yes
$(0,1,5)$	no ( $\mathbf{g}^* \mathbf{u} = 0$ )
$(1,0,10)$	no ( $\mathbf{g}^* \mathbf{u} = 0$ )

### gliding dislocations

in the basal plane

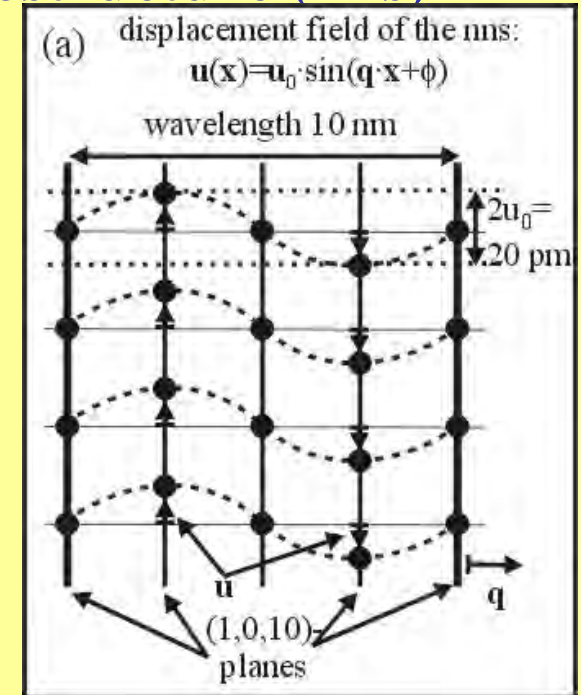
density  $10^9 \text{cm}^{-2}$

Burgers vector  $[1,1,0]$



## Structure model for the natural nanostructure (nns)

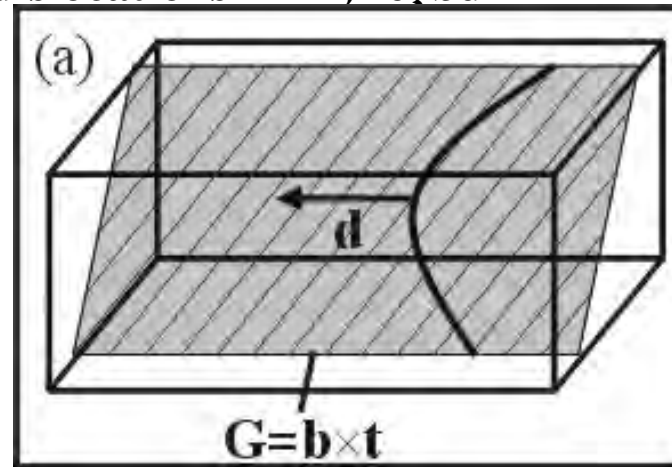
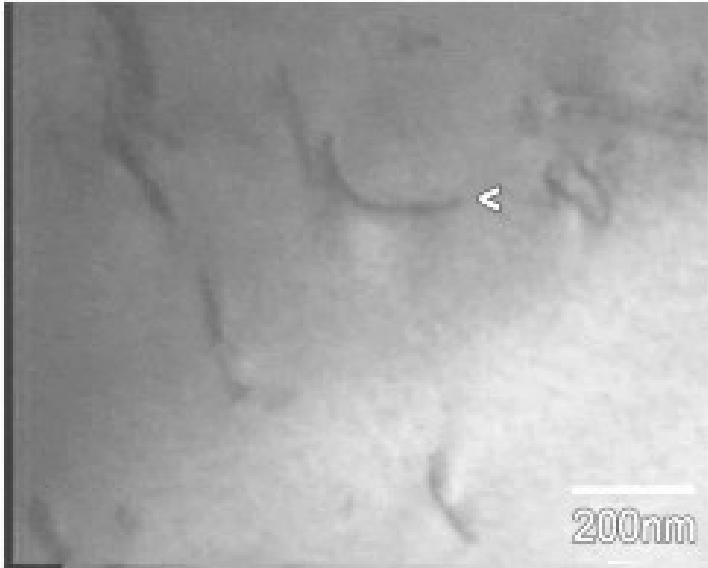
1. A structural modulation (nns) is superimposed to the average structure and can be imaged using the  $\{-1,0,5\}$  reflections.
2. The nns is of general character for  $\text{Bi}_2\text{Te}_3$  materials: n-type and p-type bulk materials.
3. The origin of the nns is a pure structural modulation with wavelength of 10 nm, wave vector  $\{1,0,10\}$ , displacement vector  $\langle 5,-5,1 \rangle$ , and an amplitude of 10 pm.
4. Rejected models for the nns: chemical modulations and ordered network of non basal plane dislocations



## Thermoelectric properties and the nns

1.  $\text{Bi}_2\text{Te}_3$  shows a  $\lambda_{\text{latt}}$  like highly disordered materials, the nns is a significant structural disorder. Lattice thermal conductivity should be decreased due to phonon scattering on the sinusoidal strain field of the nns.
2. The nns should yield a one-dimensional or zero-dimensional behaviour and anisotropic transport coefficients in the basal plane.
3. The number of nns and thereby the thermoelectric properties might be controlled by the thermal history of the sample.

## Gliding dislocations in Bi,Te, bulk



Burgers vector  $\mathbf{b}$ , line direction  $\mathbf{t}$ , glide plane  $\mathbf{G}$ , direction of motion  $\mathbf{d}$

- gliding at room temperature and without applied shear stresses
- an activation energy has thermally to be overcome to start and maintain motion
- basal plane as glide plane,  $\mathbf{b} = \langle 1, 0, 0 \rangle$

### Lattice thermal conductivity at 3 K

$\lambda_{\text{latt}}$  according to literature

transport theory for isotropic solids:

$$\lambda_{\text{latt}} = \frac{1}{3} C \cdot v \cdot l_{\text{ph}}$$

phonon mean free path and dislocation density  $N$ :

$$l_{\text{ph}} = \frac{0.455}{\gamma^2 k_D} \frac{\theta_D}{T} \frac{1}{b^2 N}$$

230 W/mK

729  $\mu\text{m}$

832  $\mu\text{m}$

→ agreement

15 W/mK

48  $\mu\text{m}$

832  $\mu\text{m}$

→ no agreement

→ more sources for phonon scattering

## Gliding dislocations in $\text{Bi}_2\text{Te}_3$

1. Dislocations in the basal plane with a high mobility at room temperature were found. The motion was induced by heating with a focused electron beam. External stresses were not applied.
2. Stereomicroscopy investigations combined with image simulations yielded basal plane dislocations with a density of  $10^9 \text{ cm}^{-2}$  and Burgers vectors  $\langle 1,1,0 \rangle$ .
3. Phonon scattering on dislocations in  $\text{Bi}_2\text{Te}_3$  reduces the lattice thermal conductivity.

**N. Peranio and O.Eibl, „Gliding dislocations in  $\text{Bi}_2\text{Te}_3$  materials“, Phys. Status Solidi A 206, 42 (2009).**

## Summary

### Expected:

1. Chemical analysis established in TEM and EPMA
2. Density and character of dislocations determined
3. Specimen preparation established, particularly thin films in cross section
4. Imaging of superlattices

### Unexpected:

1. nns discovered and character explained: scattering center for phonons, role of the superlattice
2. Variations in stoichiometry: local changes of carrier density
3. Gliding dislocations at room temperature : scattering center for phonons
4. Bending of superlattices due to threading dislocations: carrier mobility

## Outlook

SPP 1386:

“Nanostructure, excitations, and thermoelectric properties of  $\text{Bi}_2\text{Te}_3$ -based nanomaterials”



# Thank You !!!

Prof. O. Eibl



Irmgard Meissner



Balaji Birajdar



Leopoldo Molina-Luna



Michael Rössel



Dominique Eyidi  
Manuela Eber-Koyuncu  
Joachim Nurnus  
Harald Böttner  
Bernhard Degel  
Dorothea Adam  
Heinz Drexler  
Prof . Wenzel  
Group of Prof. Kleiner